

Midium Power Transistors (-50V / -3A)

Structure

PNP Silicon epitaxial planar transistor

• Features

- 1) Low saturation voltage
- $V_{CE (sat)}$ = -0.4V (Max.) (I_C / I_B=-1A / -50mA) 2) High speed switching

Applications

Low Frequency Amplifier Driver

• Packaging specifications

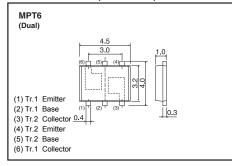
	Package	MPT6
Туре	Code	TR
	Basic ordering unit (pieces)	1000

●Absolute maximum ratings (Ta=25°C)

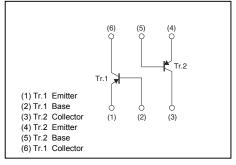
< t is the same ratings for the Tr.1 and Tr.2>

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Parameter		Symbol	Limits	Unit	
Collector-base voltage		V _{CBO}	-50	V	
Collector-emitter voltage		V _{CEO}	-50	V	
Emitter-base voltage		V _{EBO}	-6	V	
Collector current	DC	Ι _c	-3	А	
Collector current	Pulsed	۱ _{CP} ۱	-6	А	
Power dissipation		P _D *2	2.0	W/Total	
		P _D *2	1.4	W/Element	
Junction temperature		Tj	150	°C	
Range of storage temperature		T _{stg}	-55 to 150	°C	

• Dimensions (Unit : mm)



• Inner circuit (Unit : mm)



*1 Pw=10ms, Single Pulse

*2 Mounted on a 40 x 40 x 0.7[mm] ceramic board

•Electrical characteristics (Ta=25°C)

< t is the same characteristics for the Tr.1 and Tr.2>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	-50	-	-	V	I _C = -1mA
Collector-base breakdown voltage	BV_{CBO}	-50	-	-	V	Ι _C = -100μΑ
Emitter-base breakdown voltage	BV_{EBO}	-6	-	-	V	Ι _Ε = -100μΑ
Collector cut-off current	I _{CBO}	-	-	-1	μA	V _{CB} = -50V
Emitter cut-off current	I _{EBO}	-	-	-1	μA	V _{EB} = -4V
Collector-emitter staturation voltage	V _{CE(sat)} ^{*1}	-	-200	-400	mV	I _C = -1A, I _B = -50mA
DC current gain	h _{FE}	180	-	450	-	V _{CE} = -3V, I _C = -50mA
Transition frequency	f _T ^{*1}	-	300	-	MHz	V _{CE} = -10V I _E =500mA, f=100MHz
Collector output capacitance	C _{ob}	-	24	-	pF	V _{CB} = -10V, I _E =0A f=1MHz
Turn-on time	t _{on} *2	-	45	-	ns	1 - 1 = 0 = 1 = 0 = 0
Storage time	t _{stg} * ₂	-	250	-	ns	I _C = -1.5A, I _{B1} = -150mA, I _{B2} =150mA, V <u>c</u> -10V
Fall time	t _f *2	-	35	-	ns	

*1 Pulsed

*2 See switching time test circuit

•Electrical characteristic curves (Ta=25°C)

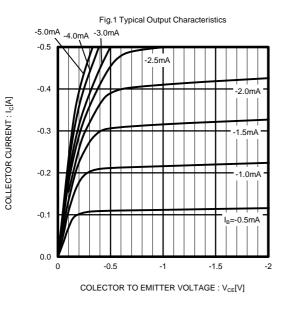


Fig.3 DC Current Gain vs. Collector Current (II)

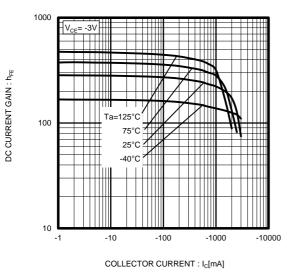


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (II)

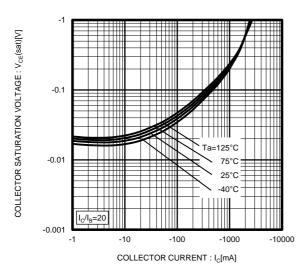


Fig.2 DC Current Gain vs. Collector Current (I)

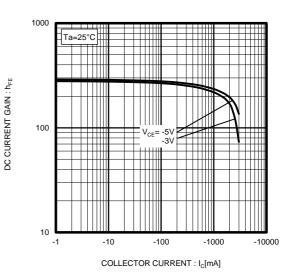
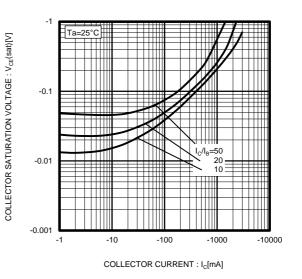
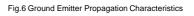
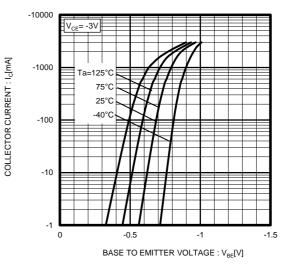
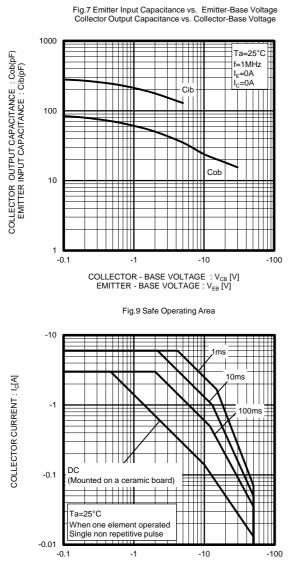


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (I)



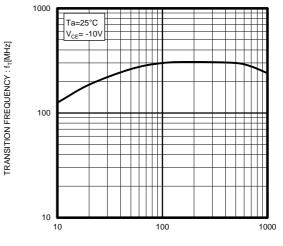






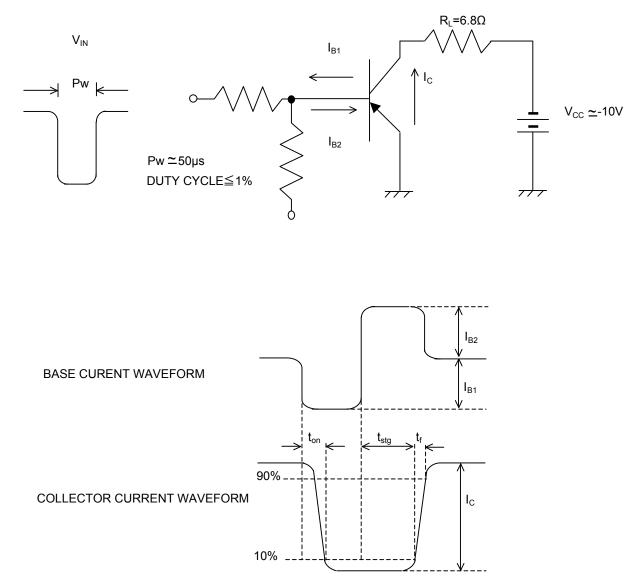
COLLECTOR TO EMITTER VOLTAGE : $V_{CE}[V]$

Fig.8 Gain Bandwidth Product vs. Emitter Current



EMITTER CURRENT : I_E[mA]

• Switching time test circuit



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